Jitsuo Ohta

List of Publications by Year
in descending order

133 papers	2,431 citations	201674 27 h-index	276875 41 g-index
135 all docs	135 docs citations	135 times ranked	1519 citing authors

#	Article	IF	Citations
1	AlN/InAlN thin-film transistors fabricated on glass substrates at room temperature. Scientific Reports, 2019, 9, 6254.	3.3	2
2	Epitaxial Growth of Thick Polar and Semipolar InN Films on Yttriaâ€Stabilized Zirconia Using Pulsed Sputtering Deposition. Physica Status Solidi (B): Basic Research, 2018, 255, 1700320.	1.5	7
3	Growth of Si-doped AlN on sapphire (0001) via pulsed sputtering. APL Materials, 2018, 6, .	5.1	7
4	Electrical properties of Si-doped GaN prepared using pulsed sputtering. Applied Physics Letters, 2017, 110, .	3.3	56
5	N-polar InGaN-based LEDs fabricated on sapphire via pulsed sputtering. APL Materials, 2017, 5, .	5.1	17
6	Low-temperature pulsed sputtering growth of InGaN multiple quantum wells for photovoltaic devices. Japanese Journal of Applied Physics, 2017, 56, 031002.	1.5	5
7	Characterization of GaN films grown on hafnium foils by pulsed sputtering deposition. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1700244.	1.8	3
8	Epitaxial growth of semipolar InAlN films on yttria-stabilized zirconia. Physica Status Solidi (B): Basic Research, 2017, 254, 1700211.	1.5	1
9	Pulsed sputtering epitaxial growth of m-plane InGaN lattice-matched to ZnO. Scientific Reports, 2017, 7, 12820.	3.3	8
10	Highly conductive Ge-doped GaN epitaxial layers prepared by pulsed sputtering. Applied Physics Express, 2017, 10, 101002.	2.4	29
11	Sputter synthesis of wafer-scale hexagonal boron nitride films via interface segregation. APL Materials, 2017, 5, .	5.1	12
12	Electron transport properties of degenerate <i>n</i>-type GaN prepared by pulsed sputtering. APL Materials, 2017, 5, .	5.1	34
13	Fabrication of full-color GaN-based light-emitting diodes on nearly lattice-matched flexible metal foils. Scientific Reports, 2017, 7, 2112.	3.3	19
14	GaN-Based Light-Emitting Diodes with Graphene Buffers for Their Application to Large-Area Flexible Devices. IEICE Transactions on Electronics, 2017, E100.C, 161-165.	0.6	3
15	Epitaxial growth of GaN films on nearly lattice-matched hafnium substrates using a low-temperature growth technique. APL Materials, 2016, 4, .	5.1	8
16	High hole mobility p-type GaN with low residual hydrogen concentration prepared by pulsed sputtering. APL Materials, 2016, 4, 086103.	5.1	55
17	High-current-density indium nitride ultrathin-film transistors on glass substrates. Applied Physics Letters, 2016, 109, 142104.	3.3	10
18	InN thin-film transistors fabricated on polymer sheets using pulsed sputtering deposition at room temperature. Applied Physics Letters, 2016, 109, 032106.	3.3	20

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19	Epitaxial growth of In-rich InGaN on yttria-stabilized zirconia and its application to metalâ€“insulatorâ€“semiconductor field-effect transistors. Journal of Applied Physics, 2016, 120, 085709.	2.5	2
20	Fabrication of InGaN thin-film transistors using pulsed sputtering deposition. Scientific Reports, 2016, 6, 29500.	3.3	15
21	Feasibility of Fabricating Large-Area Inorganic Crystalline Semiconductor Devices. , 2016, , 249-275.		0
22	Field-effect transistors based on cubic indium nitride. Scientific Reports, 2015, 4, 3951.	3.3	40
23	Investigation of anisotropic wafer bending curvature in a-plane GaN films grown on r-plane sapphire substrates. Journal of Crystal Growth, 2015, 424, 11-13.	1.5	2
24	Dramatic reduction in process temperature of InGaN-based light-emitting diodes by pulsed sputtering growth technique. Applied Physics Letters, 2014, 104, 051121.	3.3	45
25	AlGaN/GaN heterostructure prepared on a Si (110) substrate <i>via</i> pulsed sputtering. Applied Physics Letters, 2014, 104, .	3.3	29
26	Solidâ€phase epitaxy of InO<i>_x</i> N<i>_y</i> alloys via thermal oxidation of InN films on yttriaâ€stabilized zirconia. Physica Status Solidi - Rapid Research Letters, 2014, 8, 362-366.	2.4	0
27	Structural properties of GaN films grown on multilayer graphene films by pulsed sputtering. Applied Physics Express, 2014, 7, 085502.	2.4	30
28	Effect of growth stoichiometry on the structural properties of AlN films on thermally nitrided sapphire $(11ar 20)$. Physica Status Solidi - Rapid Research Letters, 2014, 8, 256-259.	2.4	13
29	Theoretical study of InN growth on Mn-stabilized zirconia (111) substrates. Thin Solid Films, 2014, 551, 110-113.	1.8	0
30	Fabrication of full-color InGaN-based light-emitting diodes on amorphous substrates by pulsed sputtering. Scientific Reports, 2014, 4, 5325.	3.3	115
31	Theoretical study of the initial stage of InN growth on cubic zirconia (111) substrates. Physica Status Solidi - Rapid Research Letters, 2013, 7, 207-210.	2.4	6
32	Band Configuration of SiO₂/m-Plane ZnO Heterointerface Correlated with Electrical Properties of Al/SiO₂/ZnO Structures. Japanese Journal of Applied Physics, 2013, 52, 011101.	1.5	3
33	Theoretical Investigation of the Polarity Determination for<i>c</i>-Plane InN Grown on Yttria-Stabilized Zirconia (111) Substrates with Yttrium Surface Segregation. Applied Physics Express, 2013, 6, 021002.	2.4	4
34	Structural Properties ofm-Plane InAlN Films Grown on ZnO Substrates with Room-Temperature GaN Buffer Layers. Applied Physics Express, 2013, 6, 021003.	2.4	7
35	Electrical properties of amorphous-Al2O3/single-crystal ZnO heterointerfaces. Applied Physics Letters, 2013, 103, 172101.	3.3	15
36	Electron mobility of ultrathin InN on yttria-stabilized zirconia with two-dimensionally grown initial layers. Applied Physics Letters, 2013, 102, 022103.	3.3	17

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37	Atomic scattering spectroscopy for determination of the polarity of semipolar AlN grown on ZnO. Applied Physics Letters, 2013, 103, .	3.3	5
38	Polarity control and growth mode of InN on yttriaâ€stabilized zirconia (111) surfaces. Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 2251-2254.	1.8	7
39	Demonstration of enhanced optical polarization for improved deep ultraviolet light extraction in coherently grown semipolar Al0.83Ga0.17N/AlN on ZnO substrates. Applied Physics Letters, 2011, 99, 121906.	3.3	1
40	Characteristics of AlN Films Grown on Thermally-Nitrided Sapphire Substrates. Applied Physics Express, 2011, 4, 015501.	2.4	11
41	Xâ€ray reciprocal space mapping study on semipolar InAlN films coherently grown on ZnO substrates. Physica Status Solidi - Rapid Research Letters, 2011, 5, 400-402.	2.4	0
42	Coherent growth of <i>r</i>â€plane GaN films on ZnO substrates at room temperature. Physica Status Solidi (A) Applications and Materials Science, 2011, 208, 834-837.	1.8	11
43	Band offsets of polar and nonpolar GaN/ZnO heterostructures determined by synchrotron radiation photoemission spectroscopy. Physica Status Solidi (B): Basic Research, 2011, 248, 956-959.	1.5	24
44	Fabrication of densely packed arrays of GaN nanostructures on nano-imprinted substrates. Journal of Crystal Growth, 2011, 319, 102-105.	1.5	1
45	Growth of group III nitride nanostructures on nano-imprinted sapphire substrates. Thin Solid Films, 2011, 519, 6534-6537.	1.8	0
46	Polarity replication across m-plane GaN/ZnO interfaces. Applied Physics Letters, 2011, 99, 181910.	3.3	4
47	Dependence on composition of the optical polarization properties of m-plane InxGa1âˆ’xN commensurately grown on ZnO. Applied Physics Letters, 2011, 99, 061912.	3.3	8
48	Polarity Dependence of Structural and Electronic Properties of Al$_{2}$O$_{3}$/InN Interfaces. Applied Physics Express, 2011, 4, 091002.	2.4	9
49	Investigation on the conversion efficiency of InGaN solar cells fabricated on GaN and ZnO substrates. Physica Status Solidi - Rapid Research Letters, 2010, 4, 88-90.	2.4	15
50	Optical polarization characteristics of <i>m</i> â€plane InGaN films coherently grown on ZnO substrates. Physica Status Solidi - Rapid Research Letters, 2010, 4, 188-190.	2.4	2
51	Structural properties of semipolar AlxGa1âˆ’xN($1ar {1}03$) films grown on ZnO substrates using room temperature epitaxial buffer layers. Physica Status Solidi (A) Applications and Materials Science, 2010, 207, 2149-2152.	1.8	11
52	Structural characteristics of semipolar InN (112<i>l</i>) films grown on yttria stabilized zirconia substrates. Physica Status Solidi (A) Applications and Materials Science, 2010, 207, 2269-2271.	1.8	4
53	Characteristics of Thickm-Plane InGaN Films Grown on ZnO Substrates Using Room Temperature Epitaxial Buffer Layers. Applied Physics Express, 2010, 3, 061001.	2.4	5
54	Improvement in the Crystalline Quality of Semipolar AlN(1ar102) Films by Using ZnO Substrates with Self-Organized Nanostripes. Applied Physics Express, 2010, 3, 041002.	2.4	4

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55	Layer-by-Layer Growth of InAlN Films on ZnO(000ar1) Substrates at Room Temperature. Applied Physics Express, 2010, 3, 021001.	2.4	13
56	Structural Characteristics of GaN/InN Heterointerfaces Fabricated at Low Temperatures by Pulsed Laser Deposition. Applied Physics Express, 2010, 3, 021003.	2.4	8
57	Electronic structures of c-plane and a-plane AlN/ZnO heterointerfaces determined by synchrotron radiation photoemission spectroscopy. Applied Physics Letters, 2010, 97, 252111.	3.3	12
58	Room-Temperature Epitaxial Growth of High-Quality m-Plane InAlN Films on Nearly Lattice-Matched ZnO Substrates. Japanese Journal of Applied Physics, 2010, 49, 070202.	1.5	12
59	Characteristics ofm-Plane InN Films Grown on ZnO Substrates at Room Temperature by Pulsed Laser Deposition. Japanese Journal of Applied Physics, 2010, 49, 080202.	1.5	3
60	Growth Orientation Control of Semipolar InN Films Using Yttria-Stabilized Zirconia Substrates. Japanese Journal of Applied Physics, 2010, 49, 080204.	1.5	5
61	Improvements in Optical Properties of Semipolarr-Plane GaN Films Grown Using Atomically Flat ZnO Substrates and Room-Temperature Epitaxial Buffer Layers. Japanese Journal of Applied Physics, 2010, 49, 100202.	1.5	0
62	Structural and Optical Properties of Nonpolar AlN(1120) Films Grown on ZnO(1120) Substrates with a Room-Temperature GaN Buffer Layer. Japanese Journal of Applied Physics, 2010, 49, 060213.	1.5	6
63	Fabrication and Characterization of AlN/InN Heterostructures. Applied Physics Express, 2009, 2, 011002.	2.4	12
64	Growth of group III nitride films by pulsed electron beam deposition. Journal of Solid State Chemistry, 2009, 182, 1241-1244.	2.9	6
65	Epitaxial growth of InN films on lattice-matched EuN buffer layers. Journal of Crystal Growth, 2009, 311, 4483-4485.	1.5	8
66	Epitaxial growth of GaN on single-crystal Mo substrates using HfN buffer layers. Journal of Crystal Growth, 2009, 311, 1311-1315.	1.5	20
67	Characteristics of InN grown directly on Al2O3 (0001) substrates by pulsed laser deposition. Journal of Crystal Growth, 2009, 311, 1316-1320.	1.5	15
68	Growth of cubic InN films with high phase purity by pulsed laser deposition. Journal of Crystal Growth, 2009, 311, 3130-3132.	1.5	8
69	Epitaxial growth of high purity cubic InN films on MgO substrates using HfN buffer layers by pulsed laser deposition. Journal of Solid State Chemistry, 2009, 182, 2887-2889.	2.9	5
70	Room temperature growth of semipolar AlN (1$ ar 1 $02) films on ZnO (1$ ar 1 $02) substrates by pulsed laser deposition. Physica Status Solidi - Rapid Research Letters, 2009, 3, 58-60.	2.4	13
71	Room-temperature epitaxial growth of high-qualitym-plane InGaN films on ZnO substrates. Physica Status Solidi - Rapid Research Letters, 2009, 3, 124-126.	2.4	14
72	Room-Temperature Epitaxial Growth of High Quality AlN on SiC by Pulsed Sputtering Deposition. Applied Physics Express, 2009, 2, 011003.	2.4	57

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73	Analysis of ITO/Mg:GaN interfaces by synchrotron radiation hard X-ray photoemission spectroscopy and their electrical characteristics. Applied Surface Science, 2008, 255, 2149-2152.	6.1	3
74	Growth and magnetic properties of zb-type MnAs films on GaAs substrates by high-temperature MBE. Journal of Crystal Growth, 2008, 310, 4535-4538.	1.5	10
75	Lowâ€temperature growth of high quality AlN films on carbon face 6Hâ€SiC. Physica Status Solidi - Rapid Research Letters, 2008, 2, 13-15.	2.4	17
76	Epitaxial growth of GaN films grown on single crystal Fe substrates. Applied Physics Letters, 2008, 93, 251906.	3.3	25
77	Growth of a-plane GaN on lattice-matched ZnO substrates using a room-temperature buffer layer. Applied Physics Letters, 2007, 91, .	3.3	22
78	Epitaxial growth of AlN films on Rh ultraviolet mirrors. Applied Physics Letters, 2007, 91, 131910.	3.3	9
79	Growth temperature dependence of structural properties of AlN films on ZnO (0001Â¯) substrates. Applied Physics Letters, 2007, 90, 141908.	3.3	14
80	Growth of single crystalline GaN on silver mirrors. Applied Physics Letters, 2007, 91, 201920.	3.3	24
81	Epitaxial growth mechanisms of AlN on SiC substrates at room temperature. Applied Physics Letters, 2007, 91, 151903.	3.3	22
82	Room temperature epitaxial growth of m-plane GaN on lattice-matched ZnO substrates. Applied Physics Letters, 2007, 90, 041908.	3.3	71
83	Epitaxial growth of nonpolar AlN films on ZnO substrates using room temperature grown GaN buffer layers. Applied Physics Letters, 2007, 91, 081915.	3.3	25
84	Low temperature epitaxial growth of GaN films on LiGaO2 substrates. Applied Physics Letters, 2007, 90, 211913.	3.3	33
85	Epitaxial growth of AlN films on single-crystalline Ta substrates. Journal of Solid State Chemistry, 2007, 180, 2335-2339.	2.9	7
86	Structural properties of GaN grown on Zn-face ZnO at room temperature. Journal of Crystal Growth, 2007, 305, 70-73.	1.5	18
87	Growth of InN films on spinel substrates by pulsed laser deposition. Physica Status Solidi - Rapid Research Letters, 2007, 1, 211-213.	2.4	1
88	Epitaxial growth of AlN on single-crystal Ni(111) substrates. Applied Physics Letters, 2006, 88, 121916.	3.3	20
89	Room temperature epitaxial growth of AlGaN on ZnO by pulsed laser deposition. Applied Physics Letters, 2006, 89, 111918.	3.3	27
90	Effects of low-temperature-grown buffers on pulsed-laser deposition of GaN on LiNbO3. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2006, 24, 2021-2024.	2.1	4

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91	Heteroepitaxial growth of GaN on atomically flat LiTaO3 (0001) using low-temperature AlN buffer layers. Journal of Crystal Growth, 2006, 293, 22-26.	1.5	6
92	Epitaxial growth of InN on nearly lattice-matched (Mn,Zn)Fe2O4. Solid State Communications, 2006, 137, 208-211.	1.9	12
93	Characteristics of InGaN with High In Concentrations Grown on ZnO at Low Temperatures. Japanese Journal of Applied Physics, 2006, 45, L611-L613.	1.5	15
94	Characteristics of Single Crystal ZnO Annealed in a Ceramic ZnO Box and Its Application for Epitaxial Growth of GaN. Japanese Journal of Applied Physics, 2006, 45, 5724-5727.	1.5	24
95	Characteristics of GaN/ZrB2Heterointerfaces Prepared by Pulsed Laser Deposition. Japanese Journal of Applied Physics, 2006, 45, 6893-6896.	1.5	8
96	Room-Temperature Epitaxial Growth of GaN on Atomically Flat MgAl2O4Substrates by Pulsed-Laser Deposition. Japanese Journal of Applied Physics, 2006, 45, L457-L459.	1.5	15
97	Characteristics of AlN/Ni(111) Heterostructures and their Application to Epitaxial Growth of GaN. Japanese Journal of Applied Physics, 2006, 45, L396-L398.	1.5	5
98	Layer-by-Layer Growth of AlN on ZnO(000$ar{1}$) Substrates at Room Temperature. Japanese Journal of Applied Physics, 2006, 45, L1139-L1141.	1.5	19
99	Room-temperature epitaxial growth of AlN on atomically flat MgAl2O4 substrates. Applied Physics Letters, 2006, 89, 182104.	3.3	18
100	Investigation of the initial stage of GaN epitaxial growth on 6H-SiC (0001) at room temperature. Applied Physics Letters, 2006, 89, 031916.	3.3	36
101	Polarity control of GaN grown on ZnO (0001Â¯) surfaces. Applied Physics Letters, 2006, 88, 181907.	3.3	69
102	Low temperature epitaxial growth of In0.25Ga0.75N on lattice-matched ZnO by pulsed laser deposition. Journal of Applied Physics, 2006, 99, 123513.	2.5	61
103	Growth temperature dependence of structural properties for single crystalline GaN films on MgAl2O4substrates by pulsed laser deposition. Semiconductor Science and Technology, 2006, 21, 1026-1029.	2.0	10
104	Heteroepitaxial growth of gallium nitride on muscovite mica plates by pulsed laser deposition. Solid State Communications, 2005, 136, 338-341.	1.9	9
105	GaN heteroepitaxial growth on LiNbO3(0001) step substrates with AlN buffer layers. Physica Status Solidi A, 2005, 202, R145-R147.	1.7	16
106	GaN Heteroepitaxial Growth on LiTaO3(0001) Step Substrates by Pulsed Laser Deposition. Japanese Journal of Applied Physics, 2005, 44, L1522-L1524.	1.5	4
107	Room-temperature epitaxial growth of GaN on lattice-matched ZrB2 substrates by pulsed-laser deposition. Applied Physics Letters, 2005, 87, 221907.	3.3	57
108	InN epitaxial growths on Yttria stabilized zirconia (111) step substrates. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2004, 22, 2487-2489.	2.1	29

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109	Room Temperature Layer by Layer Growth of GaN on Atomically Flat ZnO. Japanese Journal of Applied Physics, 2004, 43, L53-L55.	1.5	76
110	Epitaxial growth of InN on c-plane sapphire by pulsed laser deposition with r.f. nitrogen radical source. Thin Solid Films, 2004, 457, 109-113.	1.8	13
111	Structural characterization of group III nitrides grown by pulsed laser deposition. Thin Solid Films, 2004, 457, 114-117.	1.8	3
112	Effect of ambient gas on pulsed laser deposition of group III nitrides. Thin Solid Films, 2004, 457, 118-121.	1.8	1
113	Experimental and theoretical investigation on the structural properties of InN grown on sapphire. Thin Solid Films, 2004, 464-465, 112-115.	1.8	5
114	Growth temperature dependence of structural properties for AlN films grown on (Mn,Zn)Fe2O4 substrates. Thin Solid Films, 2003, 435, 218-221.	1.8	23
115	Growth of AlN on lattice-matched MnO substrates by pulsed laser deposition. Thin Solid Films, 2003, 435, 215-217.	1.8	20
116	Characteristics of AlN buffer layers for GaAs epitaxial growths on MnZn ferrite substrates. Thin Solid Films, 2003, 435, 131-134.	1.8	3
117	Low-temperature growth of AlN on nearly lattice-matched MnO substrates. Applied Surface Science, 2003, 216, 508-511.	6.1	10
118	Structural properties of GaN grown on LiGaO2 by PLD. Journal of Crystal Growth, 2003, 259, 36-39.	1.5	13
119	Experimental and theoretical investigation on the structural properties of GaN grown on sapphire. Applied Physics Letters, 2003, 83, 3075-3077.	3.3	62
120	Room-temperature epitaxial growth of GaN on conductive substrates. Applied Physics Letters, 2003, 83, 3060-3062.	3.3	55
121	Room-temperature epitaxial growth of AlN films. Applied Physics Letters, 2002, 81, 2373-2375.	3.3	84
122	Epitaxial Growth of GaN Film on (La,Sr)(Al,Ta)O3(111) Substrate by Metalorganic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2002, 41, 5038-5041.	1.5	19
123	Characterization of hetero-interfaces between group III nitrides formed by PLD and various substrates. Applied Surface Science, 2002, 190, 352-355.	6.1	29
124	Growth of GaN on nearly lattice matched MnO substrates by pulsed laser deposition. Applied Surface Science, 2002, 197-198, 384-386.	6.1	23
125	Growth of epitaxial AlN films on (Mn,Zn)Fe2O4 substrates by pulsed laser deposition. Applied Surface Science, 2002, 197-198, 486-489.	6.1	29
126	Growth of GaN on NdGaO3 substrates by pulsed laser deposition. Thin Solid Films, 2002, 407, 114-117.	1.8	38

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127	Characterization of strain distribution in quantum dots by X-ray diffraction. Journal of Crystal Growth, 2002, 234, 197-201.	1.5	21
128	CAICISS characterization of GaN films grown by pulsed laser deposition. Journal of Crystal Growth, 2002, 237-239, 1153-1157.	1.5	24
129	G-GIXD characterization of GaN grown by laser MBE. Journal of Crystal Growth, 2002, 237-239, 1158-1162.	1.5	11
130	Epitaxial growth of AlN on (La,Sr)(Al,Ta)O3 substrate by laser MBE. Journal of Crystal Growth, 2001, 225, 73-78.	1.5	54
131	Epitaxial growth of semiconductors on SrTiO3 substrates. Journal of Crystal Growth, 2001, 229, 137-141.	1.5	31
132	RHEED and XPS study of GaN on Si(111) grown by pulsed laser deposition. Journal of Crystal Growth, 2001, 233, 779-784.	1.5	41
133	Crystal Growth of GaN on (Mn,Zn)Fe2O4 Substrates. Physica Status Solidi A, 2001, 188, 497-500.	1.7	0